

**UPG90N60E** 

Preliminary

Insulated Gate Bipolar Transistor

# 600V, SMPS N-CHANNEL IGBT

#### DESCRIPTION

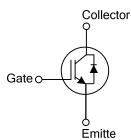
The UTC UPG90N60E is a N-channel IGBT. it uses UTC's advanced technology to provide customers with high input impedance, high switching speed and low conduction loss, etc.

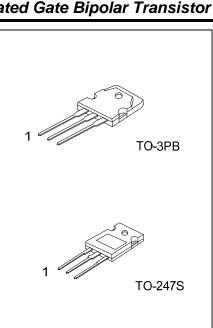
The UTC UPG90N60E is suitable for high voltage switching, high frequency switch mode power supplies.

#### **FEATURES**

- \*  $V_{CE(SAT)} \le 2.3V @ I_C=90A, V_{GE}=15V$
- \* High switching speed
- \* High input impedance
- \* Low conduction loss

#### **SYMBOL**





### **ORDERING INFORMATION**

Ordering Number		Package	Pin Assignment			Docking	
Lead Free	Lead Free Halogen Free		1	2	3	Packing	
UPG90N60EG-T3B-T	UPG90N60EG-T3B-T UPG90N60EG-T3B-T		G	С	Е	Tube	
UPG90N60EL-T47S-T	UPG90N60EL-T47S-T UPG90N60EG-T47S-T		G	С	Ш	Tube	
Note: Pin Assignment: G: Gate C: Collector E: Emitter							
	— (2)Package Type	(1) T: Tube (2) T47S: TO-247S, T3B: TO-3PB (3) G: Halogen Free and Lead Free, L: Lead Free					

### MARKING



Preliminary

#### ABSOLUTE MAXIMUM RATINGS (T<sub>c</sub>=25°C, unless otherwise specified)

		0.445.01	DATINGO	
PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage		V <sub>CES</sub>	600	V
Gate to Emitter Voltage Continuous		V <sub>GES</sub>	±20	V
Continuous Collector Current	T <sub>C</sub> =25°C		180	А
	T <sub>C</sub> =100°C		90	А
Collector Current Pulsed (Note 2)		I <sub>CM</sub>	270	А
Continuous Forward Current	T <sub>C</sub> =25°C		90	А
Continuous Forward Current	T <sub>C</sub> =100°C		45	А
Forward Current Pulsed		I <sub>FM</sub>	144	А
Peak Diode Recovery dv/dt (Note 3)		dv/dt	6.8	V/ns
	TO-247S		350	W
Power Dissipation	TO-3PB	P <sub>D</sub>	375	W
Junction Temperature		TJ	-55 ~ +150	°C
Storage Temperature Range		T <sub>STG</sub>	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. I<sub>F</sub> ≤30A, di/dt ≤200A/µs, V<sub>CC</sub> ≤ BV<sub>CES</sub>, Starting T<sub>J</sub>=25°C

### THERMAL DATA

	PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Case	TO-247S	0	0.36	°C/W
	TO-3PB	A <sup>lC</sup>	0.33	°C/W

#### ■ ELECTRICAL CHARACTERISTICS (T<sub>J</sub>=25°C, unless otherwise specified)

		-		-			
PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Collector-Emitter Breakdown Voltage	$BV_{CES}$	I <sub>C</sub> =250μA, V <sub>GE</sub> =0V		600			V
Collector-Emitter Leakage Current	I <sub>CES</sub>	V <sub>CE</sub> =600V, V <sub>GE</sub> =0V				10	μA
Gate to Emitter Leakage Current	I <sub>GES</sub>	V <sub>CE</sub> =0V, V <sub>GE</sub> =±20V				±400	nA
ON CHARACTERISTICS							
	V <sub>CE(SAT)</sub>	I <sub>C</sub> =90A, V <sub>GE</sub> =15V	TJ=25°C		1.8	2.3	V
Collector-Emitter Saturation Voltage			TJ=150°C		2.0		V
Gate to Emitter Threshold Voltage	V <sub>GE(TH)</sub>	I <sub>C</sub> =250µA, V <sub>CE</sub> =V <sub>GE</sub>		4.0		6.5	V
DYNAMIC CHARACTERISTICS							
Input Capacitance	CIES	V <sub>CE</sub> =30V, V <sub>GE</sub> =0V, f=1MHz			3730		рF
Output Capacitance	C <sub>OES</sub>				350		рF
Reverse Transfer Capacitance	C <sub>RES</sub>				64		рF
SWITCHING CHARACTERISTICS							
Total Gate Charge	$Q_{G}$	I <sub>C</sub> =90A, V <sub>CE</sub> =100V, V <sub>GE</sub> =10V			121		nC
Gate-Emitter Charge	$Q_GE$				22		nC
Gate-Collector Charge	$Q_{GC}$				55		nC
Current Turn-On Delay Time	t <sub>D(ON)</sub>		4		92		ns
Current Rise Time	t <sub>R</sub>	$I_{C}$ =90A, $V_{CE}$ =50V, $V_{GE}$ =15V, R <sub>G</sub> =10 $\Omega$			113		ns
Current Turn-Off Delay Time	t <sub>D(OFF)</sub>			2	220		ns
Current Fall Time	t <sub>F</sub>	1		256		ns	
DRAIN-SOURCE DIODE CHARACTER	ISTICS	A B	200.				
Forward Voltage Drop	V <sub>FM</sub>	I <sub>F</sub> =12A	60			3	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =12A, dl/dt=100A/µS, V <sub>CC</sub> =400V			104		ns
Reverse Recovery Charge	Q <sub>rr</sub>				330		nC
Note: Pulse Test: Pulse width≦50µs.		NN.					

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## TEST CIRCUIT AND WAVEFORMS

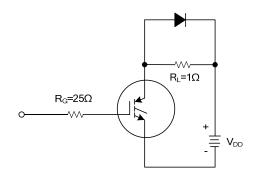


Fig 1. INDUCTIVE SWITCHING TEST CIRCUIT

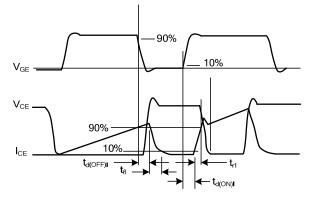


Fig 2. SWITCHING TEST WAVEFORMS

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